T.4-52011.011 01-0.0072dd13

| | | | |
|---|---|---|---|
| Average gate power dissipation ($T_j$=150 ) | $P_{G(AV)}$ | 1 | W |
| Peak gate power | $P_{GM}$ | 10 | W |
| Peak pulse voltage ($T_j$=25 ; non-repetitive,off-state;FIG.7) | $V_{pp}$ | 4.5 | kV |

($T_j$=25 unless otherwise specified) **q EMC /P <</MCI3.6 7 >>**

**FIG.1:** Maximum power dissipation versus RMS on-state current

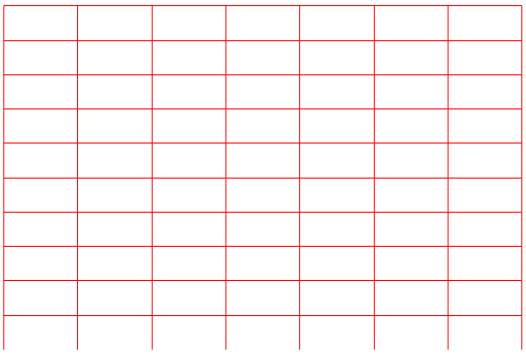
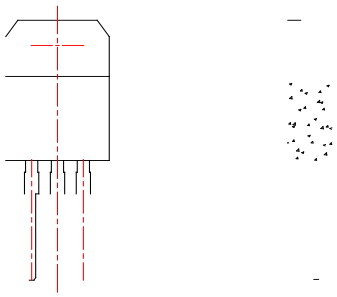


**FIG.2:** RMS on-state current versus case temperature

| Order code | Voltage $V_{DRM}/V_{RRM}$ (V) | IGT(mA) | Package | Base qty. (pcs) | Delivery mode |
|---|---|---|---|---|---|
| | | - - | | | |
| T1250H-6A | 600 | 50 | TO-220A(Ins) | 50 | Tube |

## Document Revision History

| Date | Revision | Changes |
|---|---|---|
| Apr.11, 2023 | A.1.0 | Last updated |



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